

# Operational Experience and Performance with the ATLAS Pixel detector at the Large Hadron Collider at CERN

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On behalf of the ATLAS Collaboration

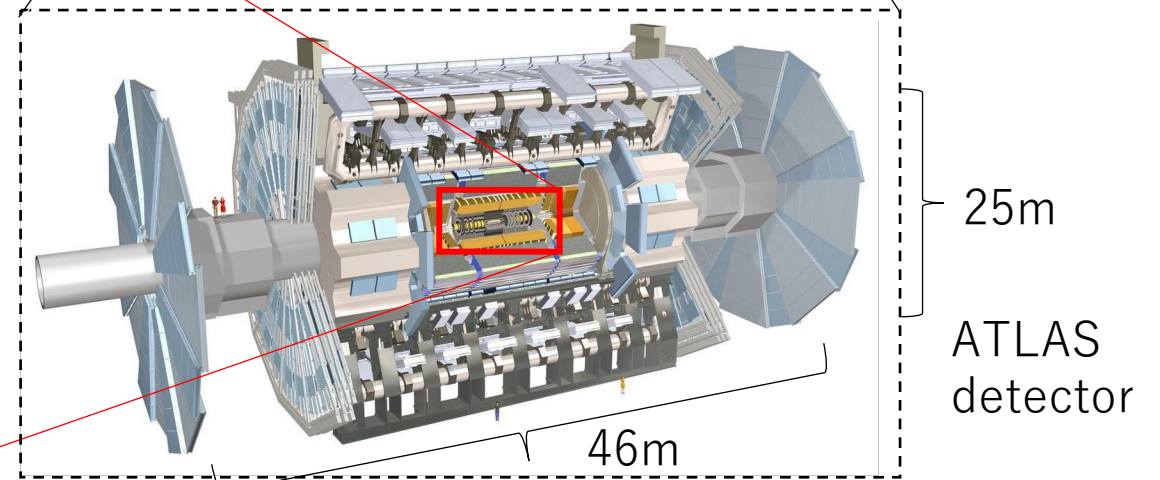
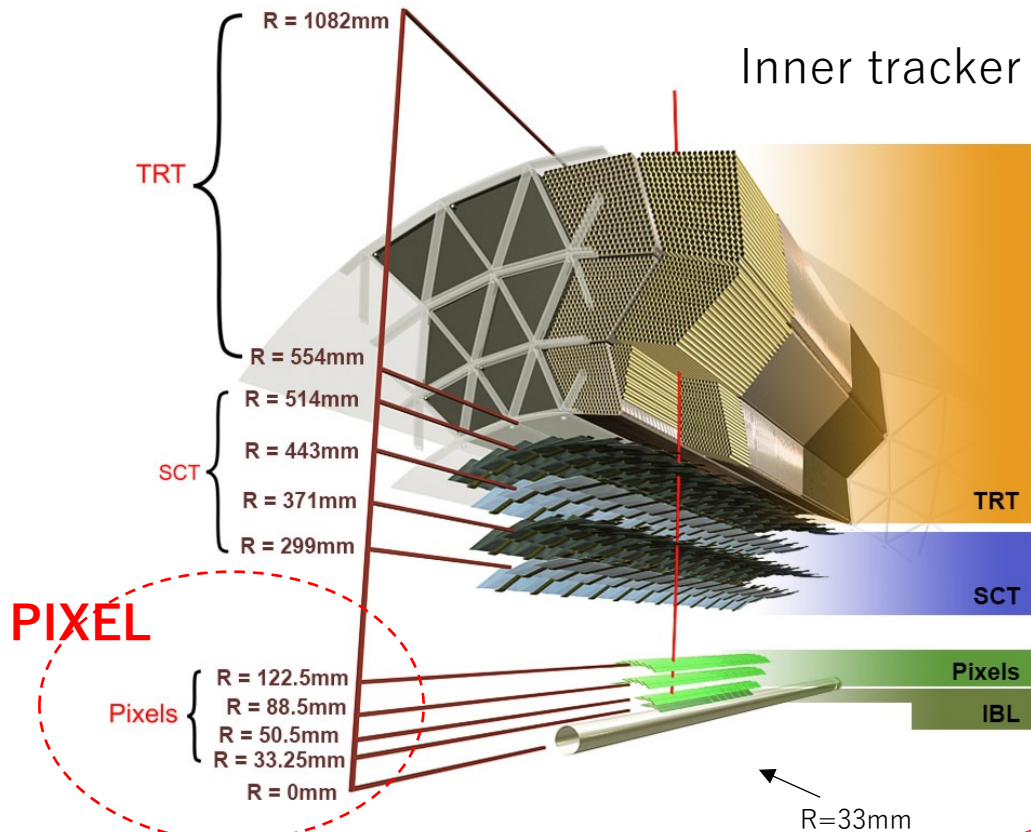
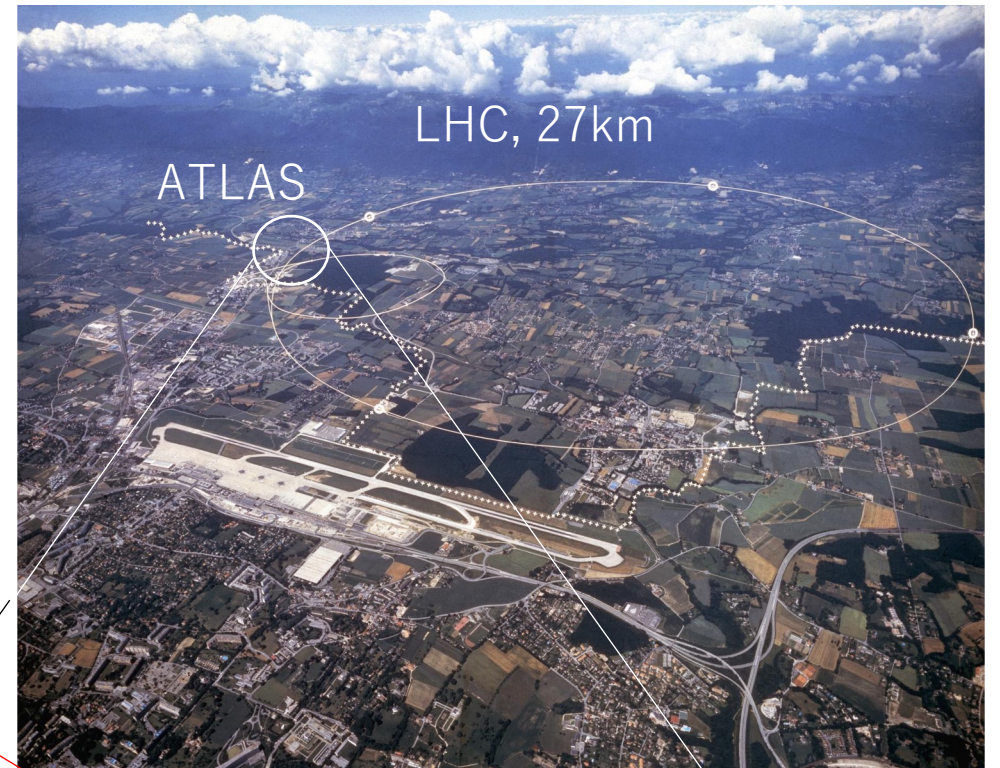


# The ATLAS Pixel detector

The ATLAS detector is located on the LHC ring.

The Pixel detector is the innermost silicon detector.

- 4 layers in the barrel + 3x2 endcap disks
- **NEW** innermost layer (**IBL**) newly used in RUN-2(2015).

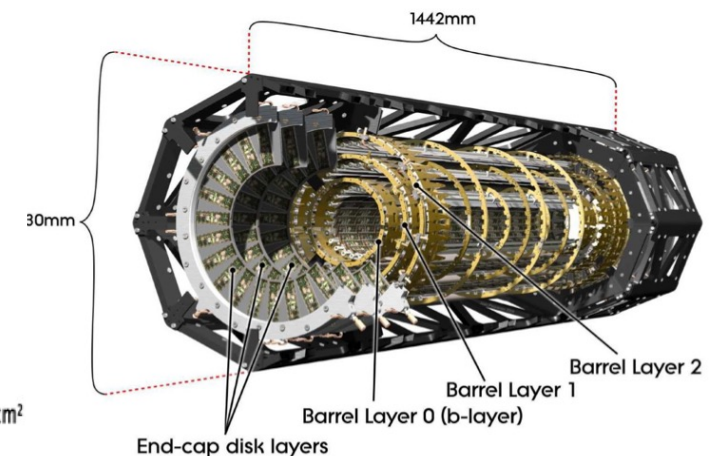
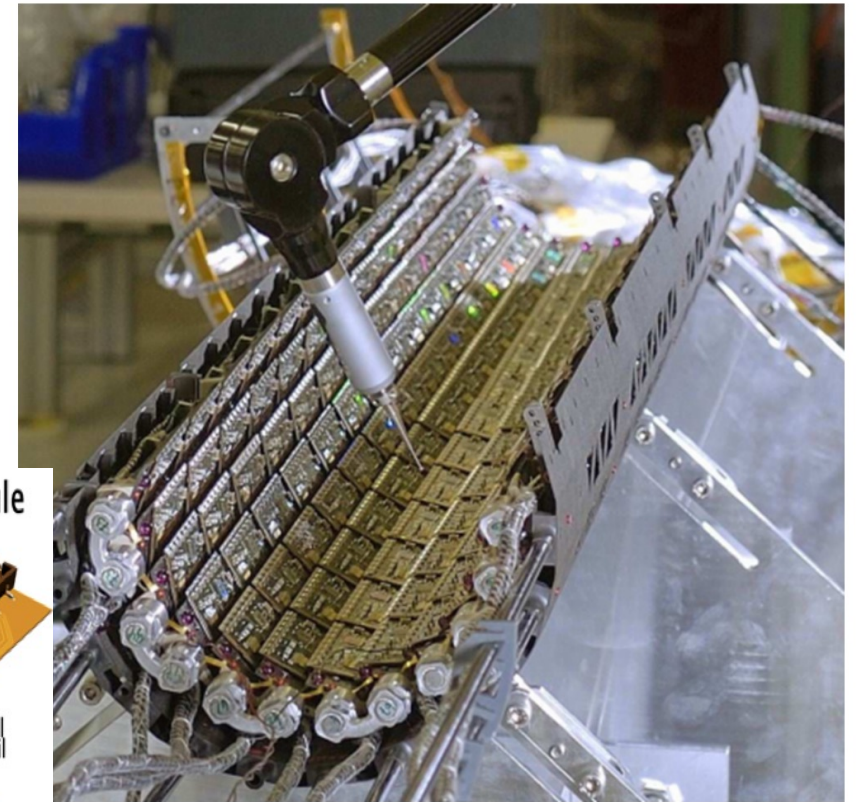
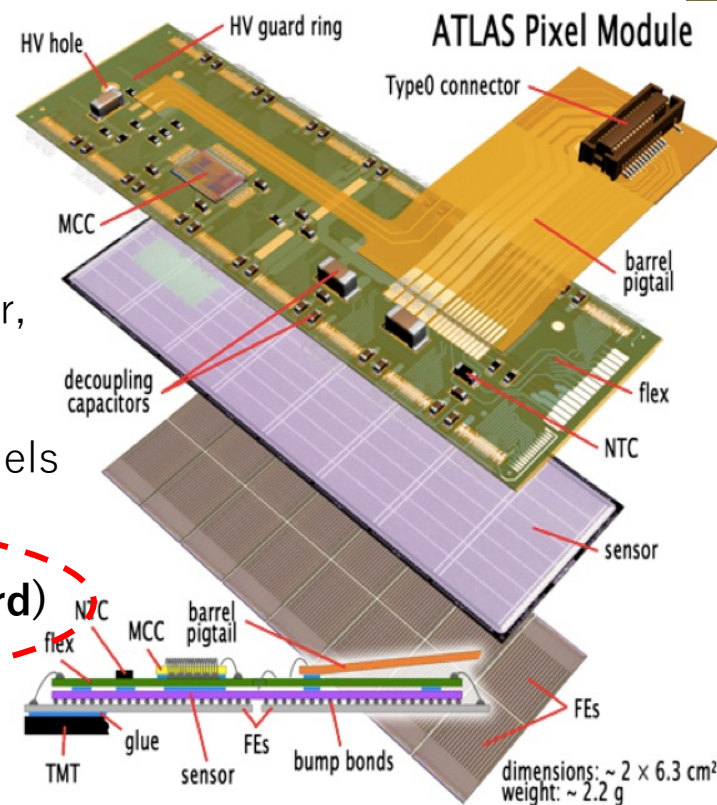


# The Outer Pixel layer

Three barrel layers, 2x3 endcap disks. (since RUN-1)  
 1744 modules (1.7m<sup>2</sup> surface), covering  $|\eta| < 2.5$ .

## Pixel module:

- Planar n<sup>+</sup>-in-n sensor,
- 60.8 x 16.4mm active area,
- 250 μm thickness,
- 16 FEI3 frontend bump-bonded on sensor,
- 50 x 400 μm<sup>2</sup> pixel size,
- Total 46080 pixels /module, ~80M channels
- 8-bit Time-over-threshold,
- Radiation hard to  $1 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$  (50Mrd)



# The IBL (Insertable B-layer)

New detector is used in RUN-2 (2015).

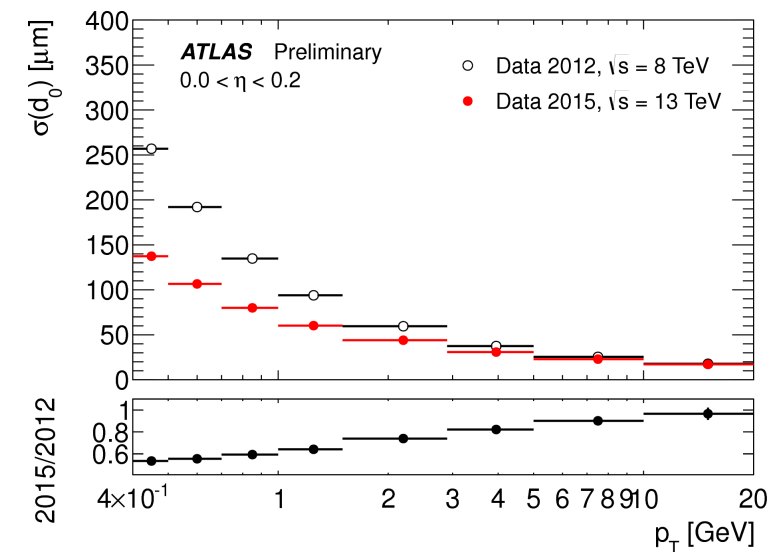
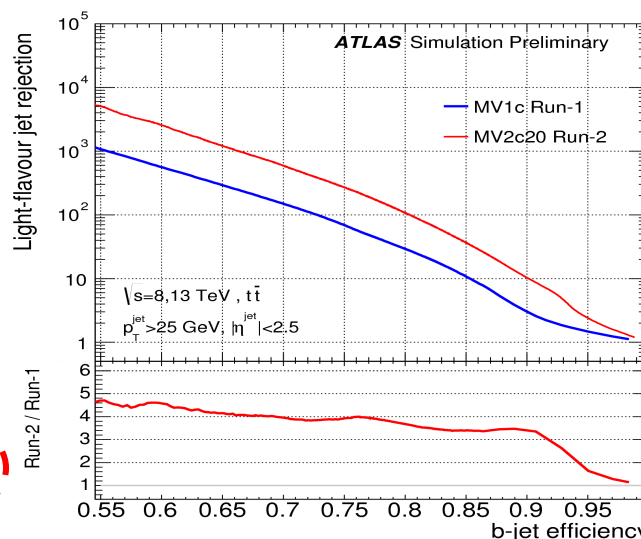
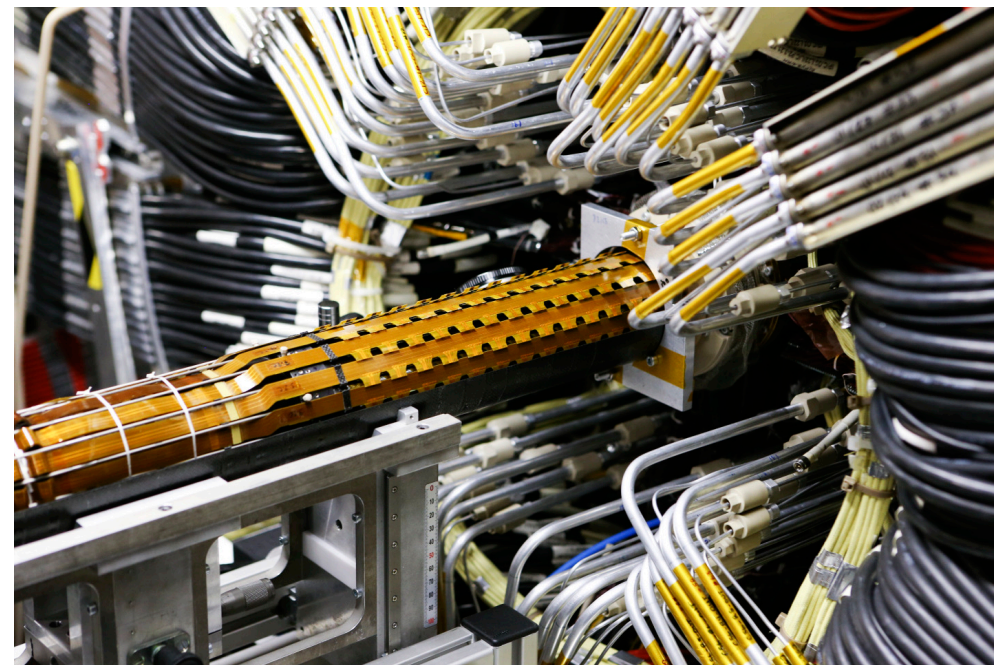
First time to use 3D sensor technology.

Located at  $R=33$  mm (just outside of beampipe (28 mm)).

5 times better rejection of b-tagging from RUN-1.

## IBL module:

- Planar  $n^+$ -in- $n$  / 3D  $n^+$ -in- $p$  sensor,
- 41.3(20.5) x 18.6 mm active area,
- 200(230)  $\mu\text{m}$  thickness (Planar/3D),
- 2(1) FEI4 chip on sensor (Planar/3D),
- 50 x 250  $\mu\text{m}^2$  pixel size,
- Total 26880 pixels / chip,  $\sim 12\text{M}$  channels,
- 4-bit Time-over-threshold,
- Radiation hard to  **$5 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$  (250Mrd)**



# Major changes in RUN3

## Optoboard replacement:

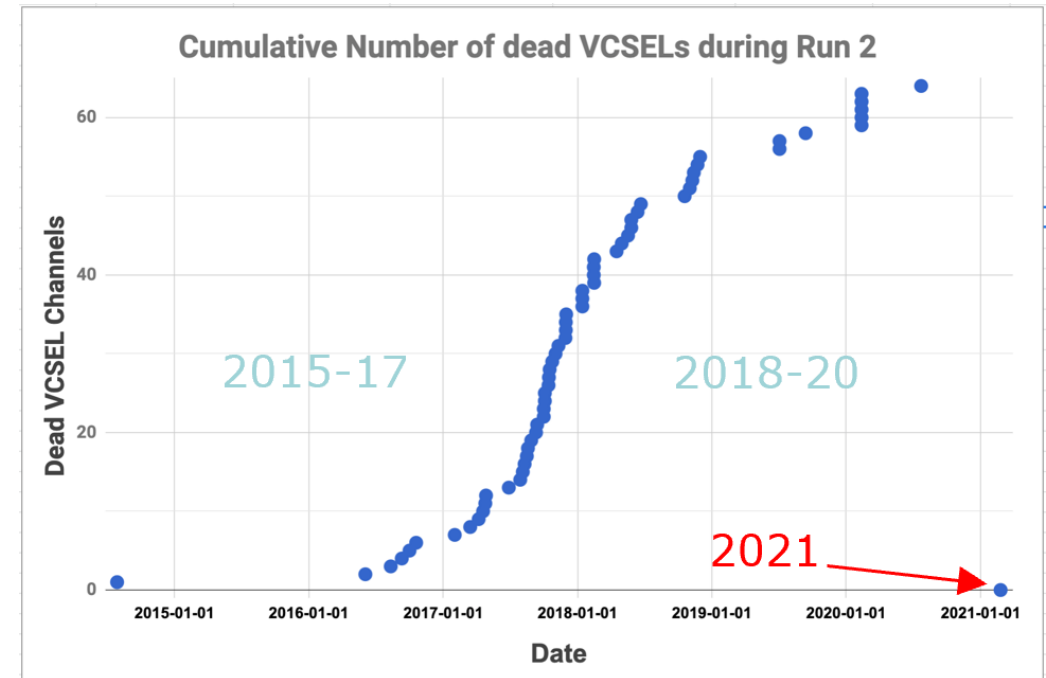
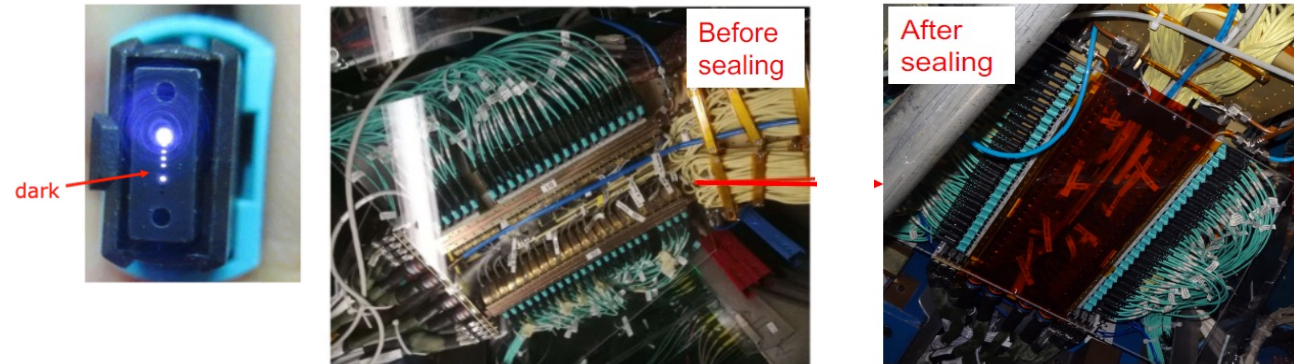
During RUN2, number of disabled modules were increased due to optoboard failure.

**~50% disabled modules were caused by this.**

➔ Suspect humidity.

Most of optoboards were replaced during LS2.

**No new failure is seen since then (RUN3).**



# Major changes in RUN3

## Software upgrade:

Employ radiation damage simulation.

RUN1 (2010-2012) : Default G4 (conventional energy loss)

RUN2 (2015-2018) : Introduction of Nuclei interaction in sensor (Bichsel model [Nucl.Instrum.Meth. A899 \(2018\) 1](#))

RUN3 (2022 -- ) : Introduction of Ramo potential (trapping of electron/hole during drift [JINST 14 \(2019\) P06012](#))

## Radiation damage:

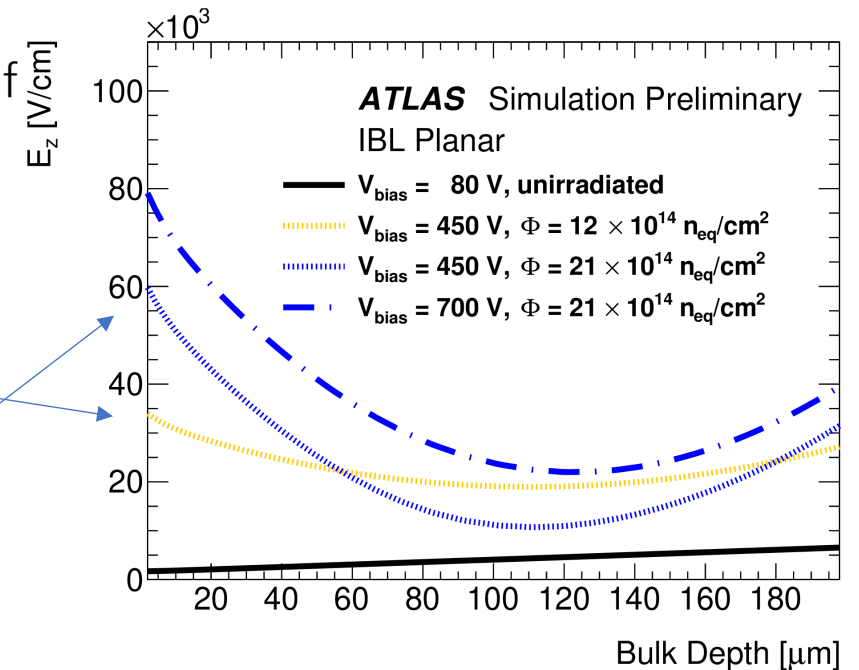
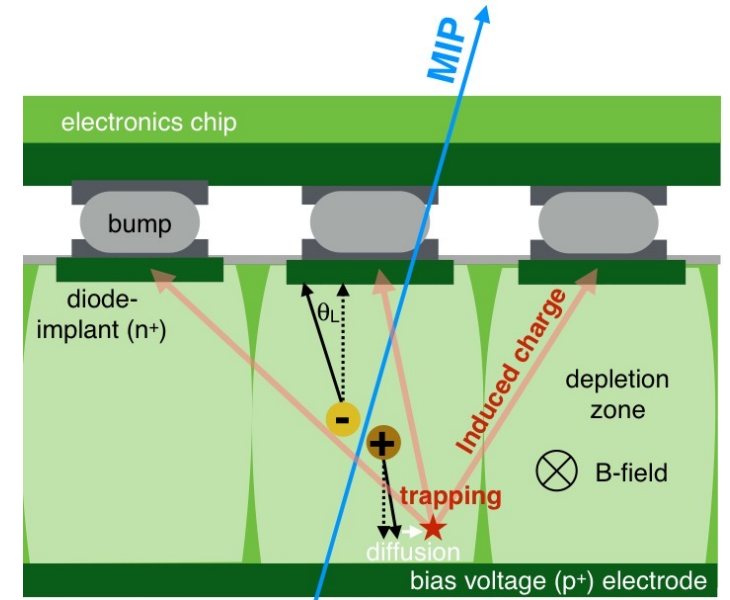
IBL :  $\sim 1.2 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$  (current, 2024)

$2.1 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$  (expected in end of RUN3 (2025))

ITk L0 :  $18 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2 @ 2000 \text{ fb}^{-1}$

ITk L2-4 :  $1 \sim 4 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2 @ 4000 \text{ fb}^{-1}$

Same order of the ITk Outer barrel

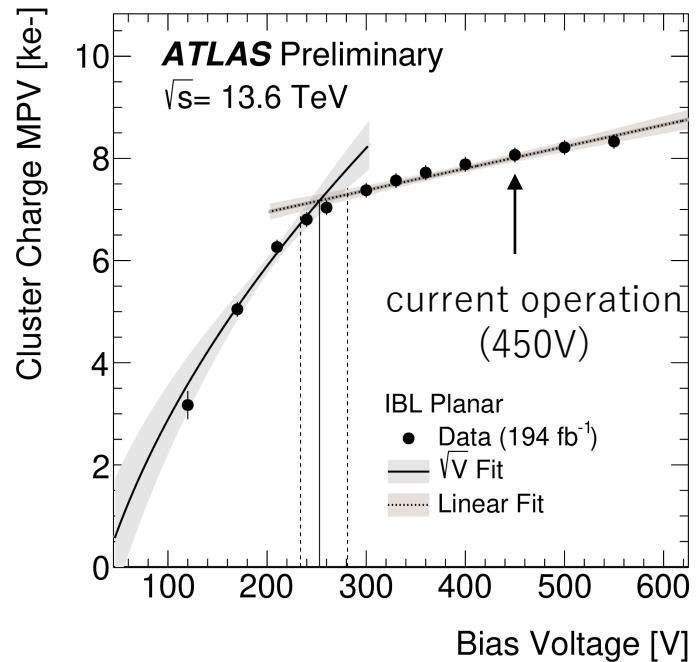


evolution ↓

# HV and threshold tuning

## Keep high hit-on-track efficiency:

- HV needs to be **increased** to operate at full-depletion voltage.
- Threshold could be **lowered**, but trade-off by the **readout error rate**.



	IBL	B-layer	Layer-1	Layer-2	Disks	
Run-2	2015	80V/2500e	250V/3500e	150V/3500e	150V/3500e	150V/3500e
	2016	80V/2500e	350V/3500e	200V/3500e	150V/3500e	150V/3500e
	2017	350V/2500e	350V/3500e	200V/3500e	150V/3500e	150V/4500e
Run-3	2018	400V/2000e	400V/4300e	250V/3500e	250V/3500e	250V/3500e
	2022	450V/1500e	450V/3500e	300V/3500e	300V/3500e	300V/3500e
	2023	450V/1500e	450V/4700e	350V/4300e	350V/4300e	350V/4300e
	2024	450V/1500e	500V/4700e	350V/4300e	350V/4300e	350V/4300e

# Operation highlight

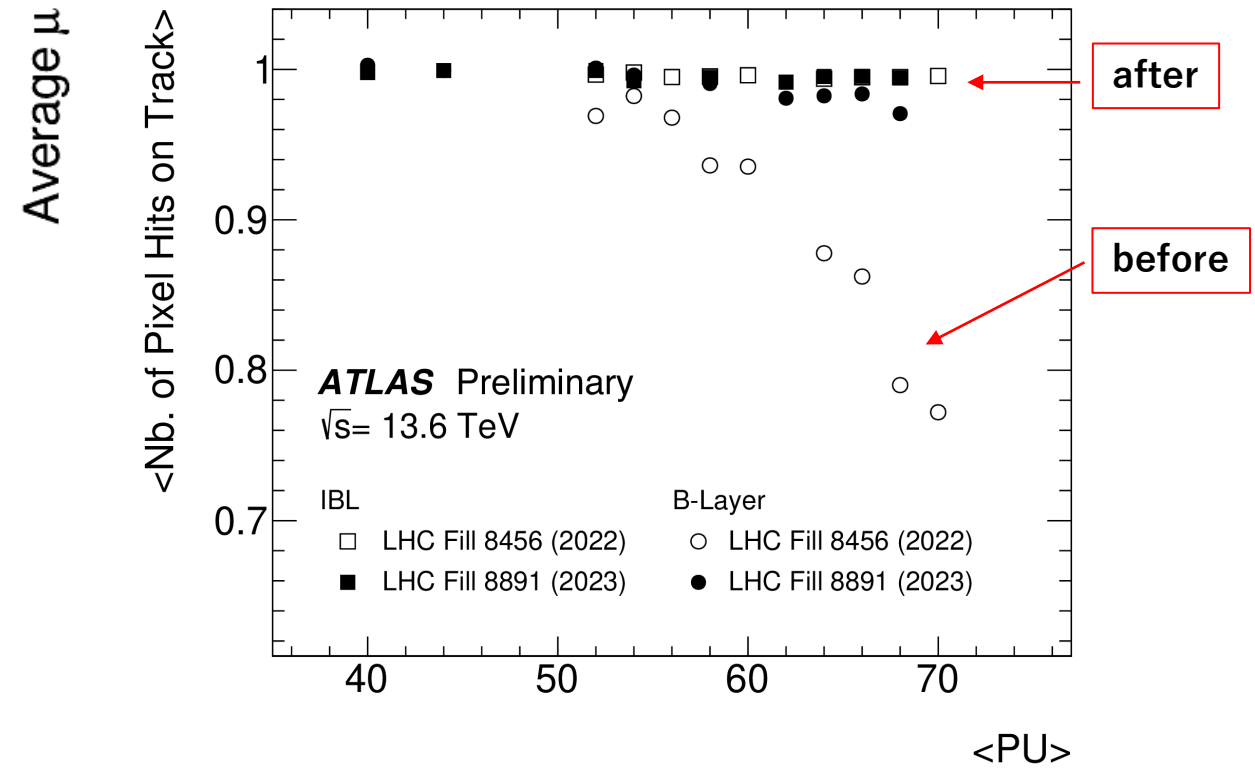
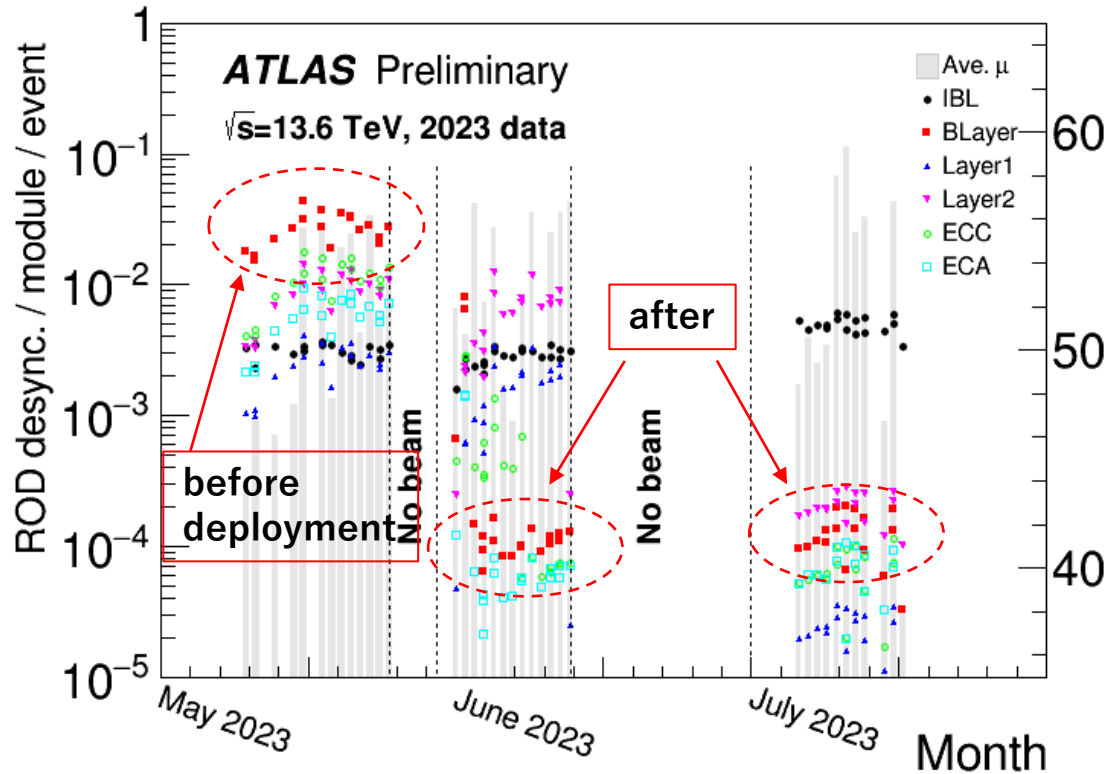
## Desynchronization error:

Pixel/IBL can **handle up to 16 triggers at a time**. Once a trigger has been missed, the module will be desynchronized until the next ATLAS event counter reset (ECR) every 5 sec.



## Solution:

In case  $>16$  triggers, the trigger command is not sent to the module in firmware. In this way, only these triggers are missed, but others are kept without waiting for ECR.

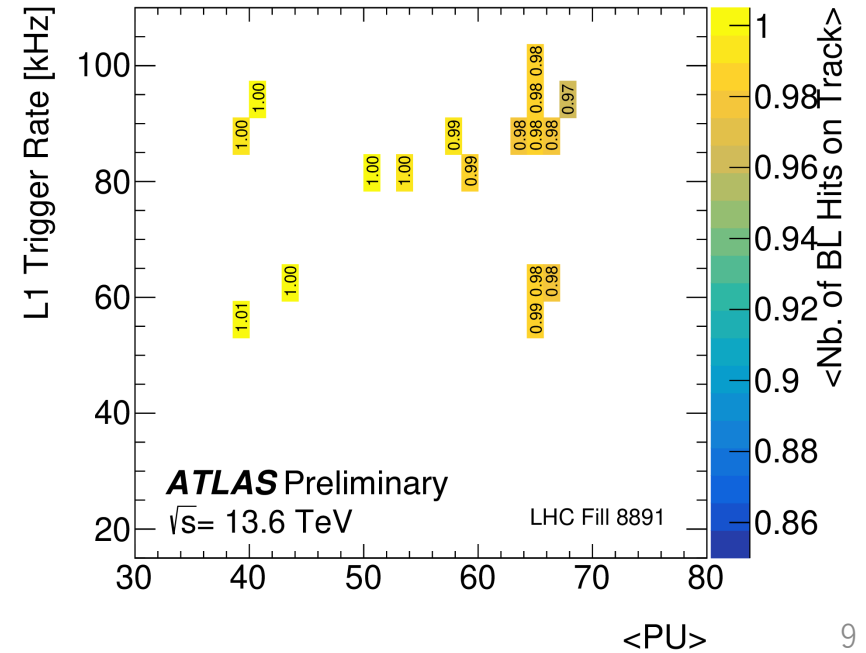
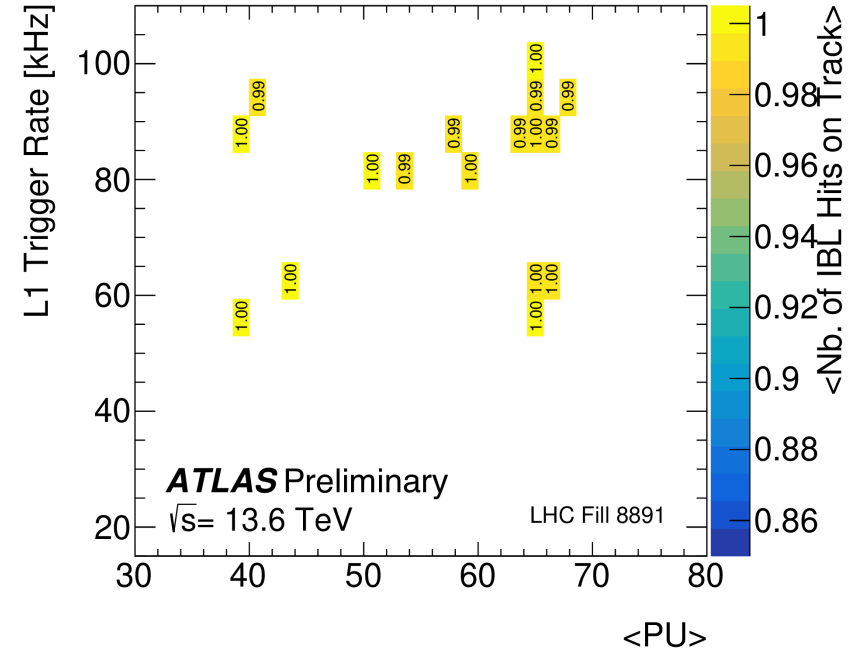
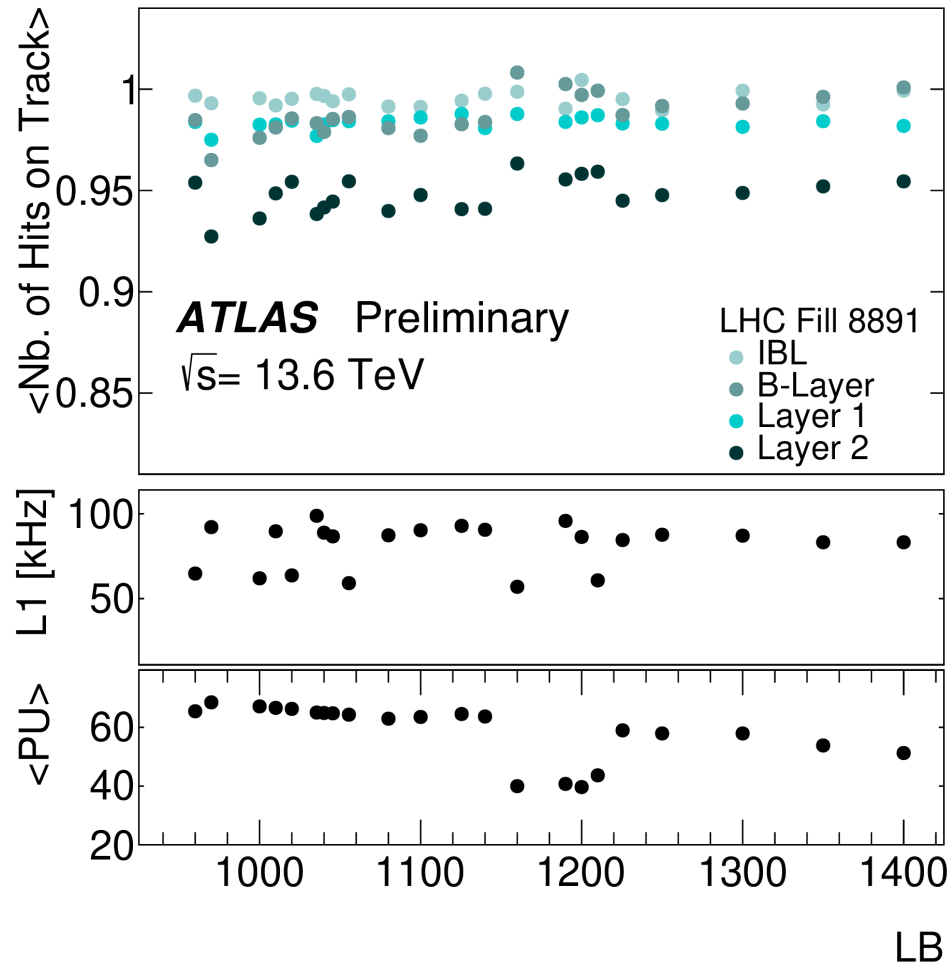




# Operation highlight

Average number of pixel hits-on-track

Demonstrates the stability over the run / pileup.

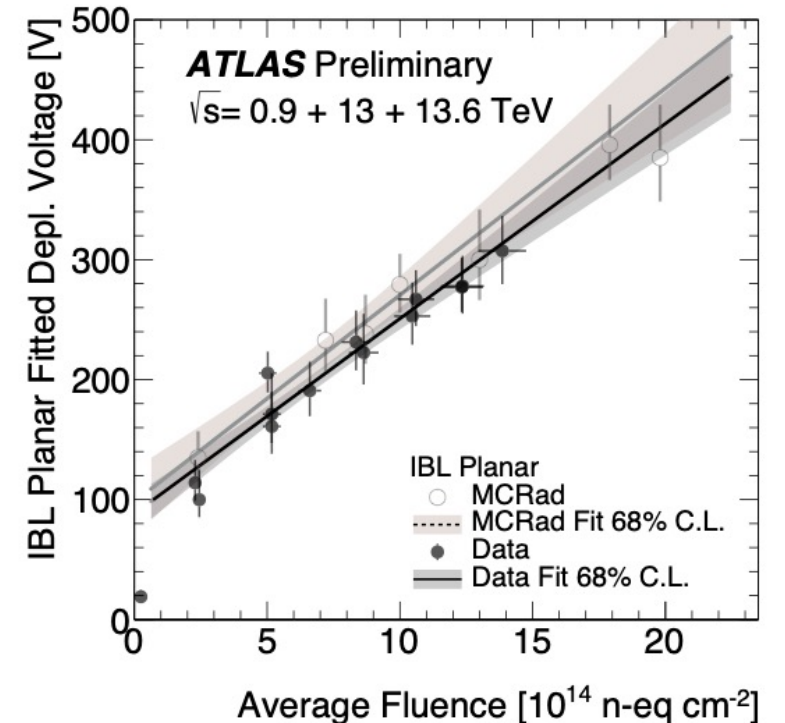
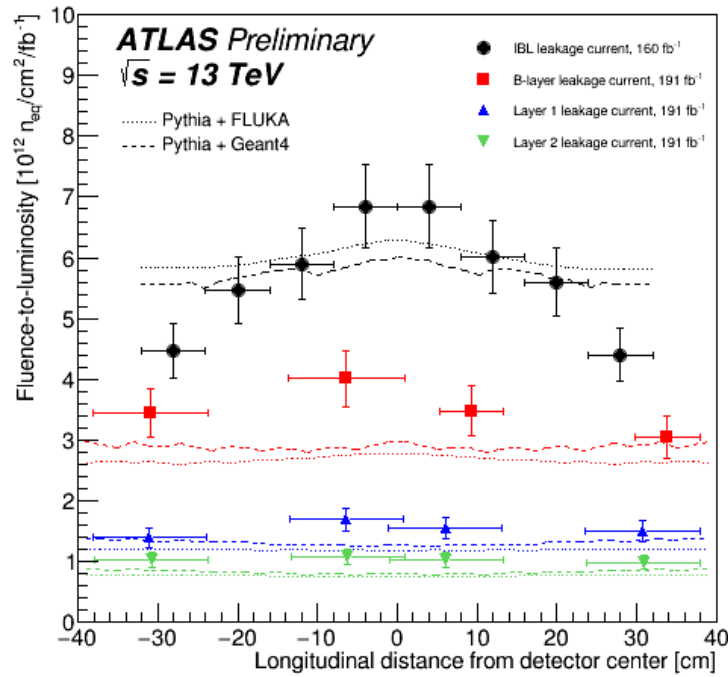
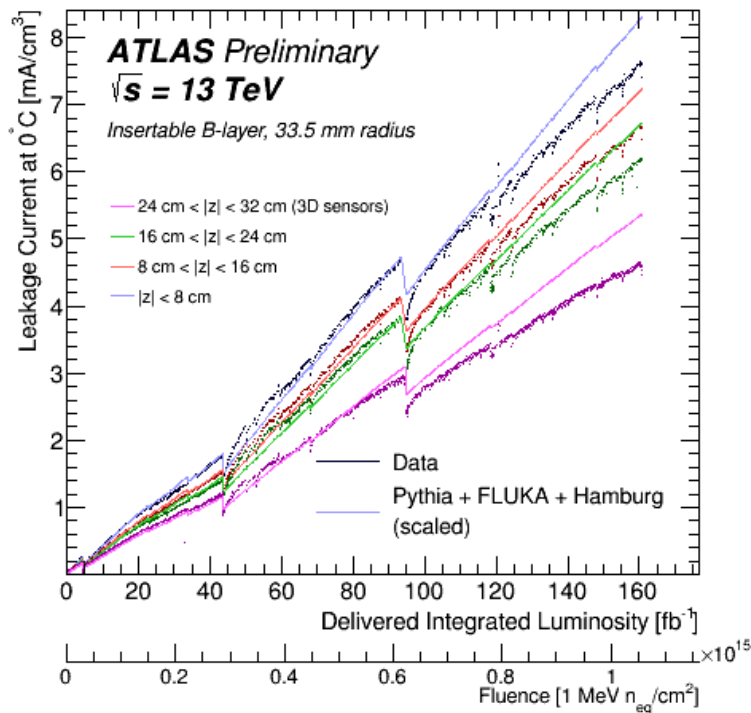


# Leakage current and fluence

The leakage current evolution is compared with Hamburg model.

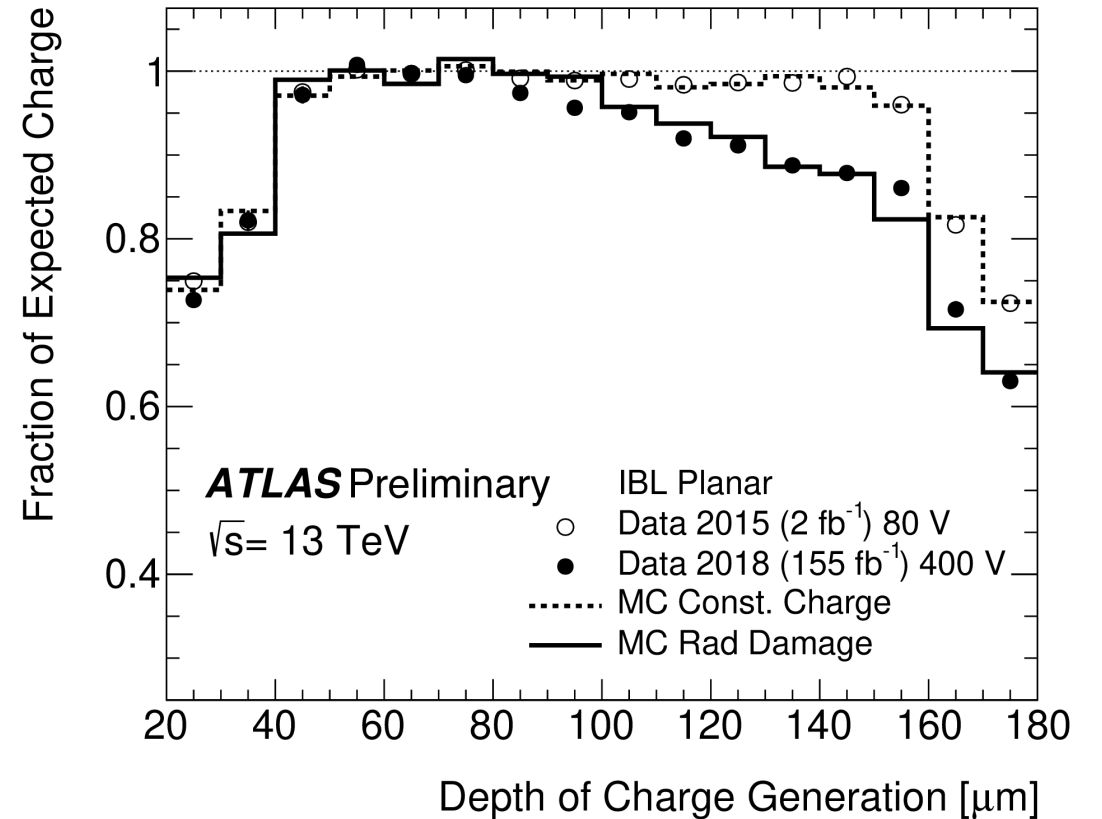
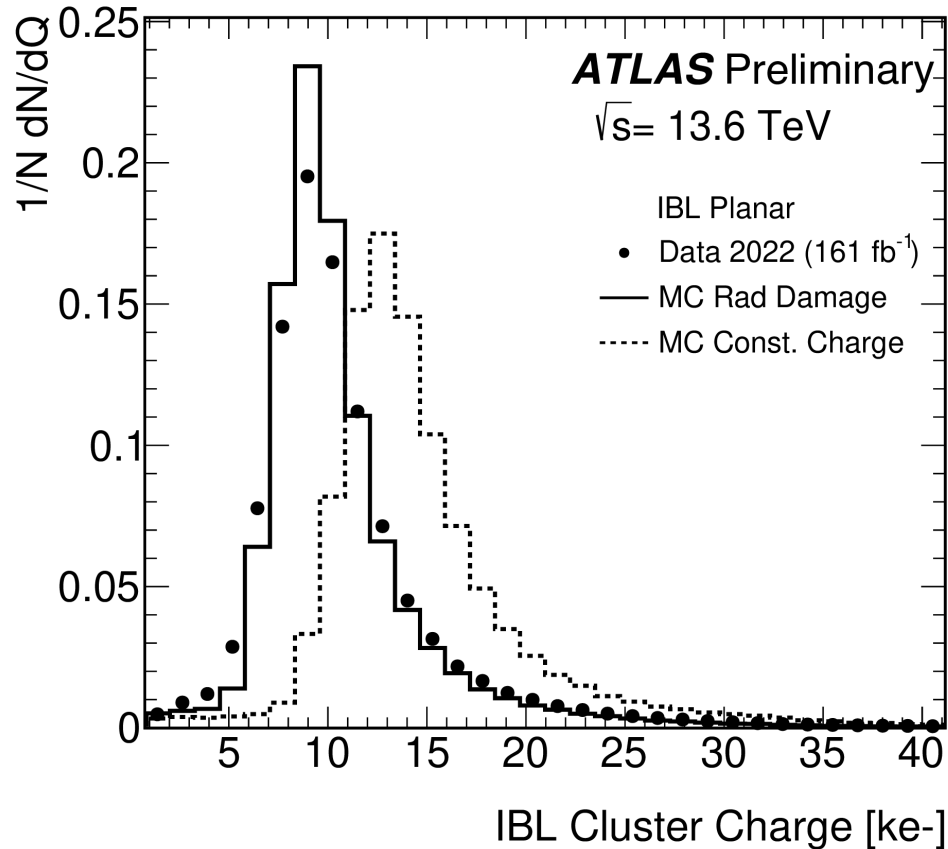
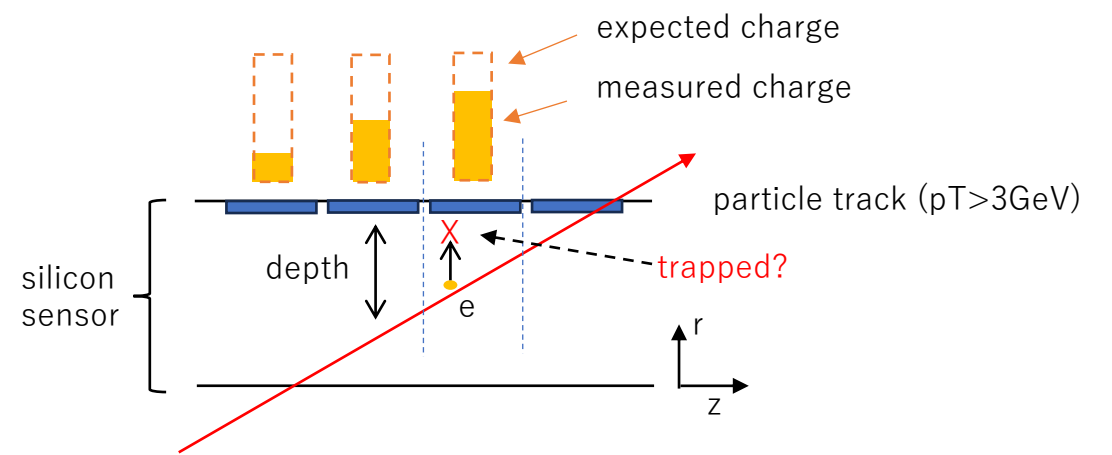
Large z-dependence in leakage current measurement, while not in MC (FLUKA/G4).

The z-dependence is also confirmed by the HV scan data.



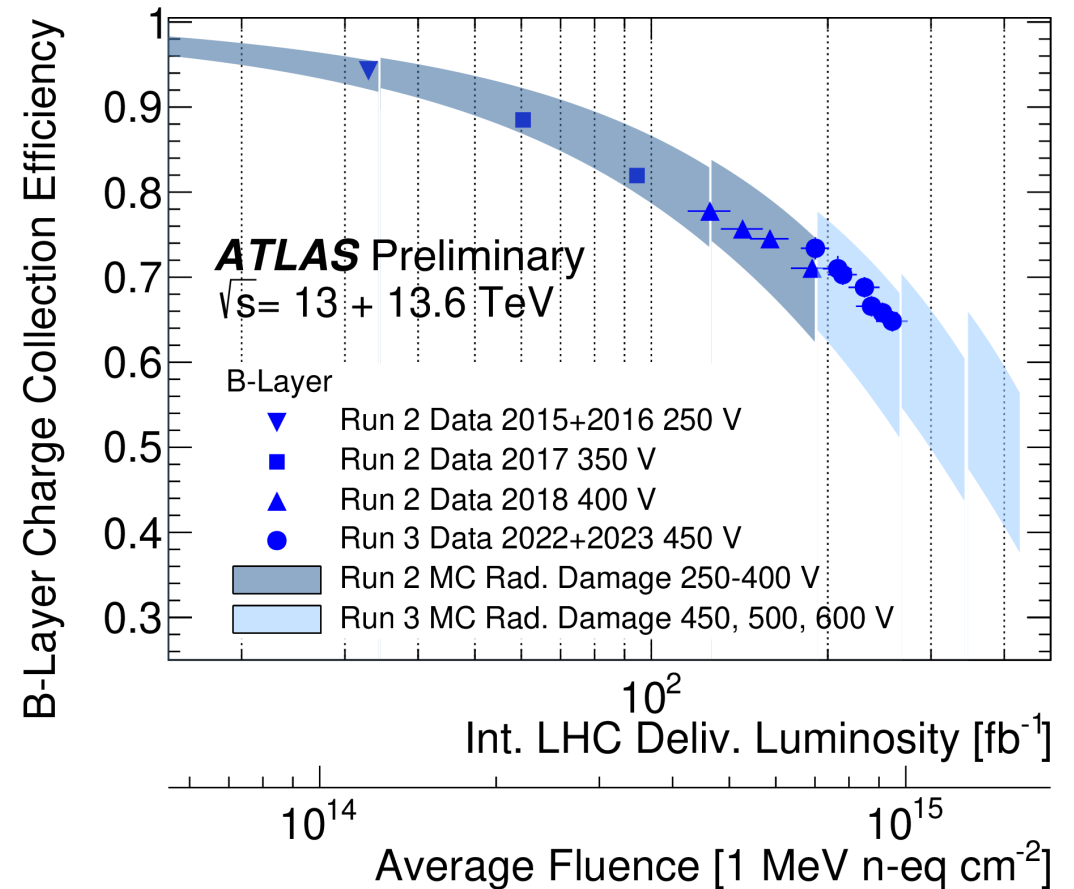
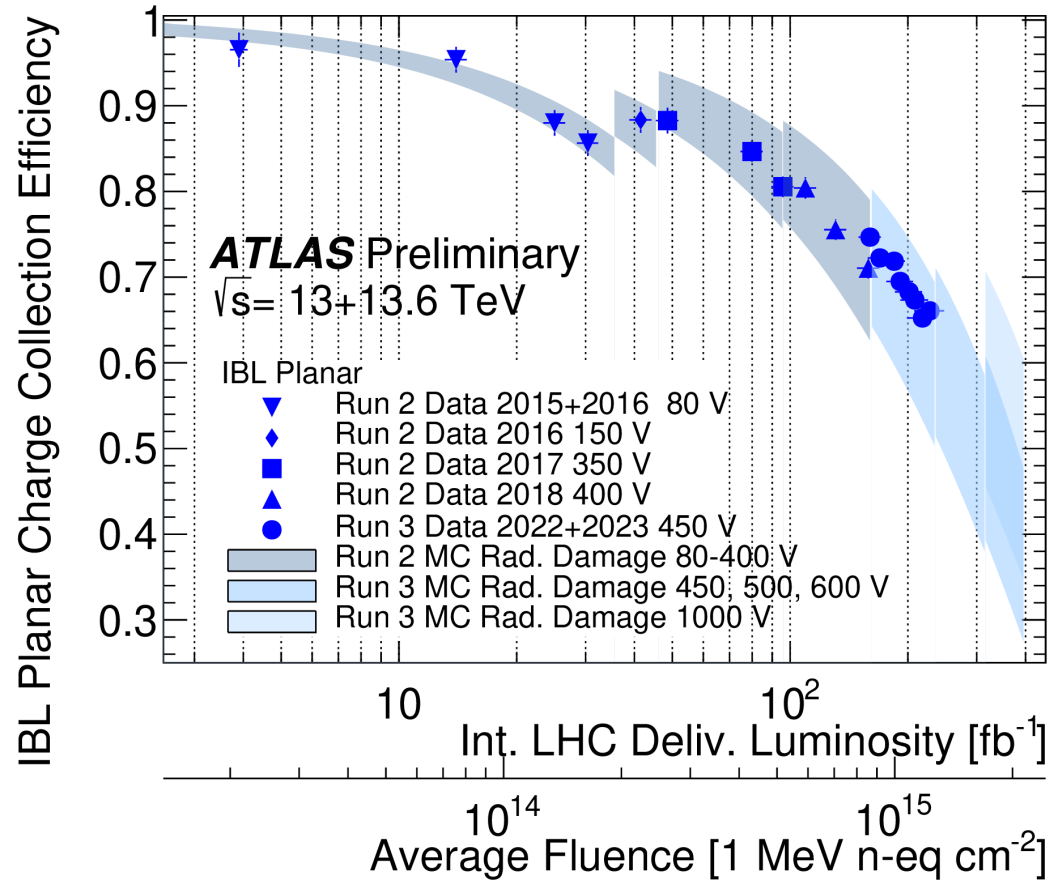
# Pixel performance

New simulation agrees with data.



# Radiation damage effect

In the end of RUN3 ( $\sim 400\text{fb}^{-1}$ ), the charge collection efficiency is kept by  $\sim 50\%$ .



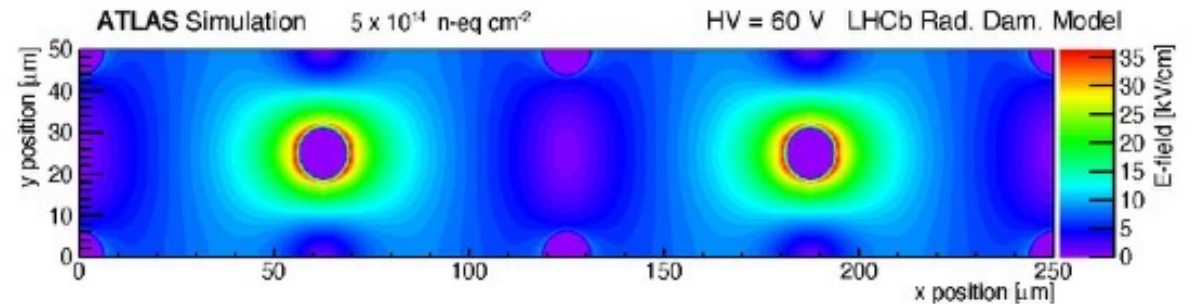
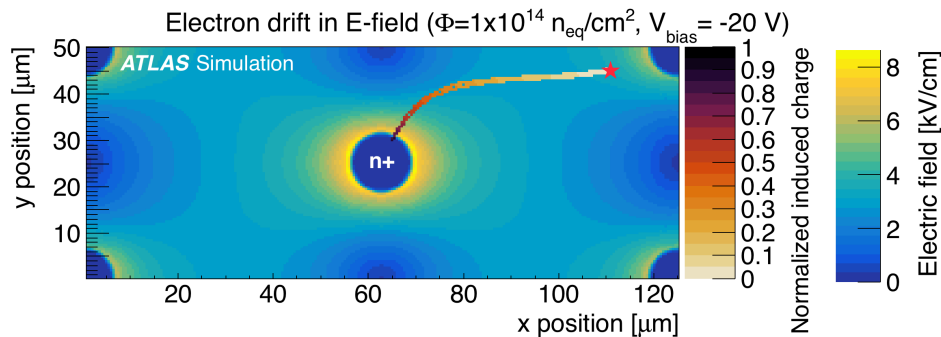
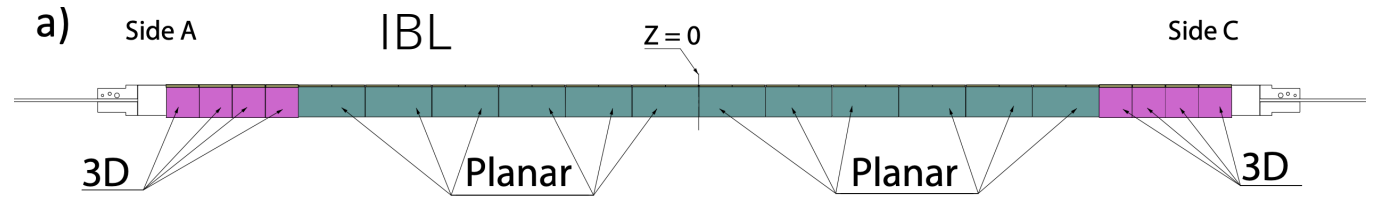
# 3D pixel sensor

The 3D sensor technology is first time used in HEP experiments.

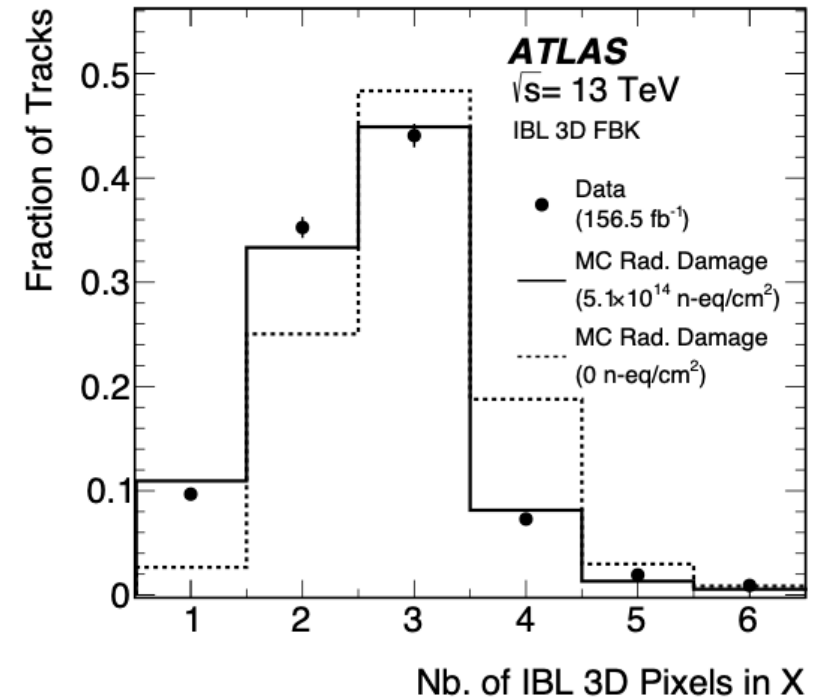
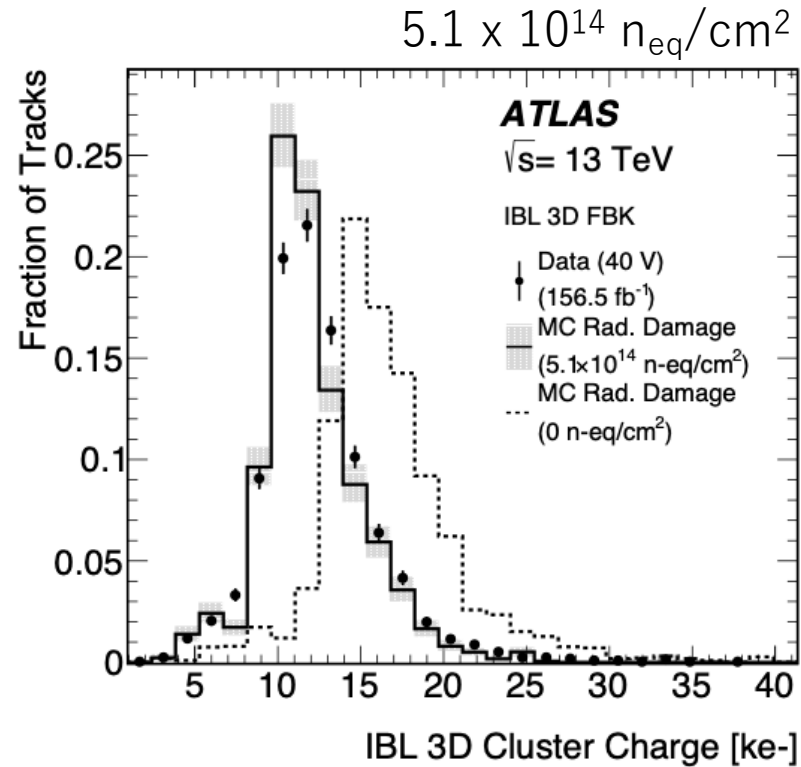
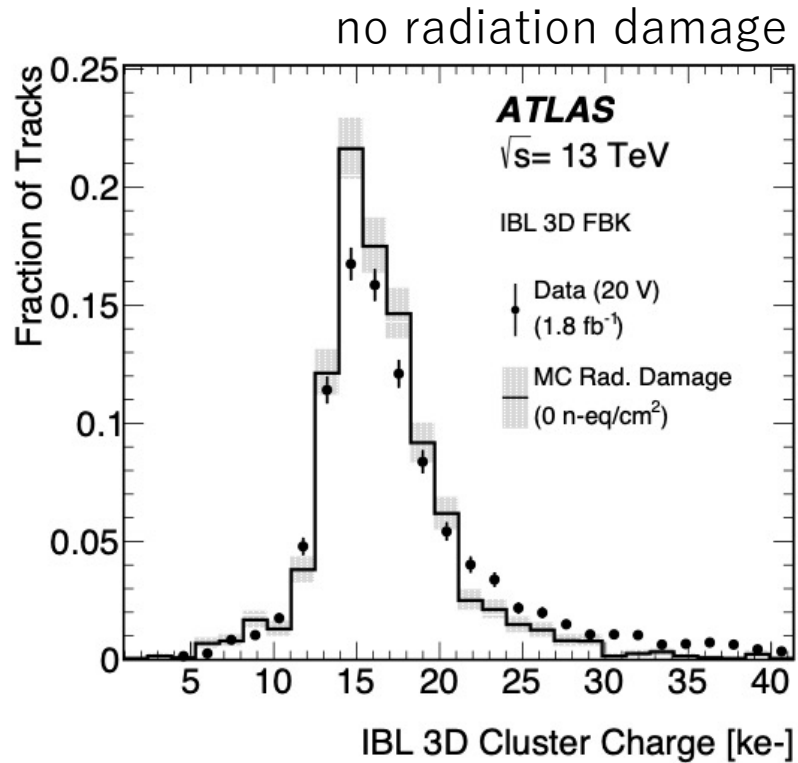
- Located in the outer end in inner-most-layer
- Two fabrications are adopted: FBK and CNM.

## Simulation:

- E-field is generated by TCAD for given fluence.
- Profiling the electron-hole drift as look-up-table.



# 3D pixel performance

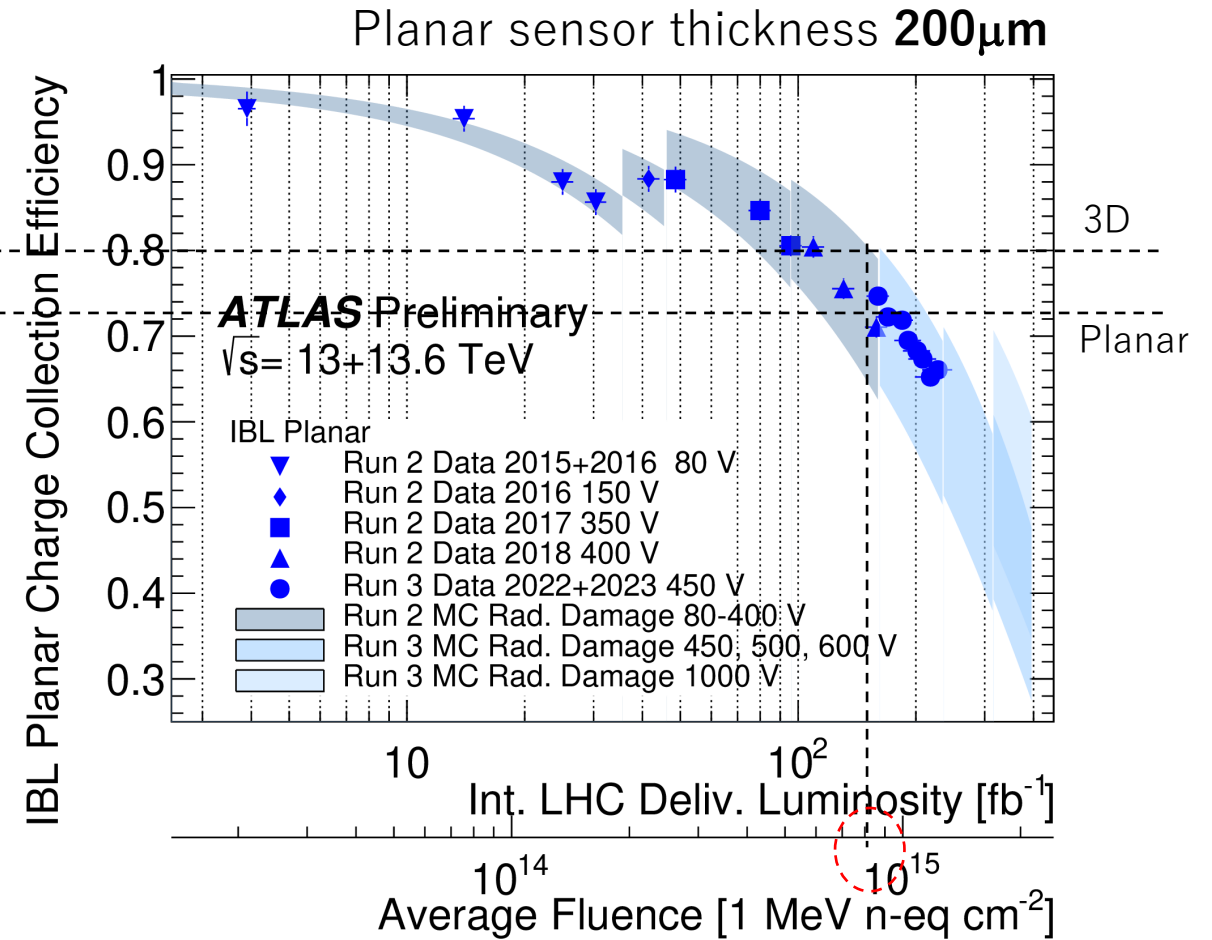
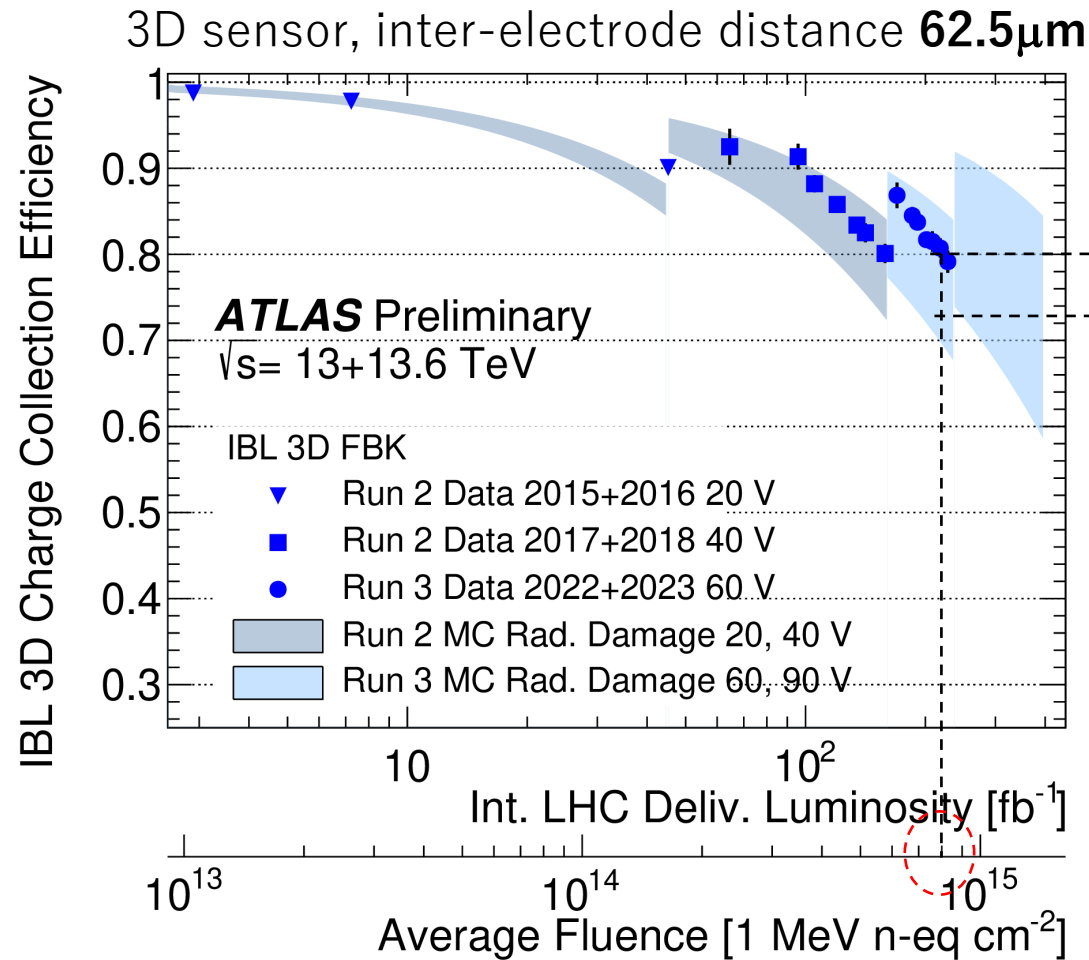


# 3D sensor radiation damage effect

Submitted to JINST

<https://arxiv.org/abs/2407.05716>

The 3D sensor is more radiation hard than planar sensor.



# Summary

So far, the pixel operation is very stable in RUN3.

## **Reported in this presentation:**

- Optoboard replacement
- Reduction of synchronization errors in outer pixel layers
- Deployment of the radiation damage simulation
- Leakage current measurements
- First results of 3D sensor performance

## **Yet important developments (not reported):**

- Reduction of the hole by finer masking at FE-level
- Deployment of several firmware reset machinery to avoid SEU
- Handling bytestream errors in the tracking
- Light weight of DB contents
- etc...

**The Run-3 experiment will be successful.**



# Backup

